

Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application.

Listing of Claims:

Claims 1-35 (Canceled)

36. (Previously presented) A capacitor adapted for use in a semiconductor device, comprising:

a first layer in the form of a plate comprising a material that serves as a barrier against the diffusion of impurities from a lower substrate;

a second layer disposed on a top surface of the first layer, such that side surfaces of the first layer remain exposed, the second layer comprising a material that is easy to pattern; and

a third layer disposed on top and side surfaces of the second layer and on the exposed side surfaces of the first layer, the third layer comprising a material having low leakage current properties.

37. (Previously presented) The capacitor of claim 36, wherein the lower substrate exposed by the third layer is overetched.

38. (Previously presented) The capacitor of claim 36, wherein the first layer comprises TiN.

39. (Previously presented) The capacitor of claim 36, wherein the second layer comprises RuO₂.

40. (Previously presented) The capacitor of claim 36, wherein the third layer comprises Pt.

41. (Previously presented) A semiconductor device, comprising:
an insulating film disposed on a semiconductor substrate;
a conductive plug disposed in the insulating film;
a first layer disposed on the conductive plug and the insulating film, the first layer comprising a material that serves as a barrier against the diffusion of impurities from the conductive plug and the semiconductor substrate;
a second layer disposed on a top surface of the first layer, such that side surfaces of the first layer remain exposed, the second layer comprising a material that is easy to pattern; and
a third layer disposed on top and side surfaces of the second layer and on the exposed side surfaces of the first layer, the third layer comprising a material having low leakage current properties.

42. (Previously presented) The capacitor of claim 41, wherein the insulating film exposed by the third layer is overetched.

43. (Previously presented) The capacitor of claim 41, wherein the first layer comprises TiN.

44. (Previously presented) The capacitor of claim 41, wherein the second layer comprises RuO₂.

45. (Previously presented) The capacitor of claim 41, wherein the third layer comprises Pt.